

IGBT - Power, Co-PAK, N-Channel, Field Stop VII (FS7), SCR, Power TO247-4L 1200 V, 1.45 V, 40 A AFGH4L40T120RWD

Description

Using the novel field stop 7th generation IGBT technology and the Gen7 Diode in TO247 4-lead package, this device offers the optimum performance with low on state voltage and minimal switching losses for both hard and soft switching topologies in automotive applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Maximum Junction Temperature – $T_J = 175^{\circ}\text{C}$
- Short Circuit Rated and Low Saturation Voltage
- Fast Switching and Tightened Parameter Distribution
- AEC-Q101 Qualified, PPAP Available Upon Request
- These Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- Automotive E-compressor
- Automotive EV PTC Heater
- OBC

MAXIMUM RATINGS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

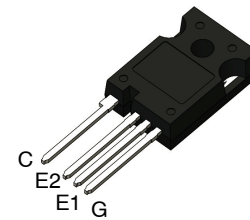
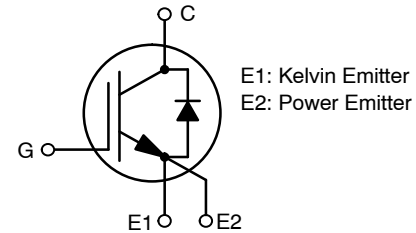
Parameter	Symbol	Value	Unit
Collector-to-Emitter Voltage	V_{CE}	1200	V
Gate-to-Emitter Voltage	V_{GE}	± 20	
Transient Gate-to-Emitter Voltage		± 30	
Collector Current	$T_C = 25^{\circ}\text{C}$	80	A
	$T_C = 100^{\circ}\text{C}$	40	
Power Dissipation	$T_C = 25^{\circ}\text{C}$	576	W
	$T_C = 100^{\circ}\text{C}$	288	
Pulsed Collector Current	$T_C = 25^{\circ}\text{C}$, $t_p = 10 \mu\text{s}$ (Note 1)	I_{CM}	120
Diode Forward Current	$T_C = 25^{\circ}\text{C}$	I_F	80
	$T_C = 100^{\circ}\text{C}$		40
Pulsed Diode Forward Current	$T_C = 25^{\circ}\text{C}$, $t_p = 10 \mu\text{s}$ (Note 1)	I_{FM}	120
Short Circuit Withstand Time $V_{GE} = 15 \text{ V}$, $V_{CC} = 800 \text{ V}$, $T_C = 150^{\circ}\text{C}$	T_{SC}	6	μs
Operating Junction and Storage Temperature Range	T_J , T_{stg}	-55 to $+175$	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes	T_L	260	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature

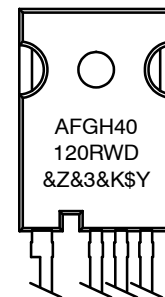
BV_{CES}	$V_{CE(sat)}$ TYP	I_C MAX
1200 V	1.45 V	40 A

PIN CONNECTIONS



TO-247-4LD
CASE 340CJ

MARKING DIAGRAM



AFGH40120RWD = Specific Device Code
 &Z = Assembly Plant Code
 &3 = 3-Digit Date Code
 &K = 2-Digit Lot Traceability Code
 \$Y = onsemi Logo

ORDERING INFORMATION

Device	Package	Shipping
AFGH4L40T120RWD	TO-247-4L (Pb-Free)	30 Units / Rail

AFGH4L40T120RWD

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case for IGBT	$R_{\theta JC}$	0.26	°C/W
Thermal Resistance, Junction-to-Case for Diode	$R_{\theta JC}$	0.46	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	1200	–	–	V
Collector-to-Emitter Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES} / \Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 9.99\text{ mA}$	–	1226	–	mV/°C
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	–	–	40	μA
Gate-to-Emitter leakage Current	I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	–	–	±400	nA

ON CHARACTERISTICS

Gate-to-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 40\text{ mA}, T_J = 25^\circ\text{C}$	4.98	5.88	6.78	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 25^\circ\text{C}$	–	1.45	1.78	V
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^\circ\text{C}$	–	1.75	–	

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{IES}	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	4713	–	pF
Output Capacitance	C_{OES}		–	195	–	pF
Reverse Transfer Capacitance	C_{RES}		–	23.8	–	pF
Total Gate Charge	Q_G	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 40\text{ A}$	–	171	–	nC
Gate-to-Emitter Charge	Q_{GE}		–	42.2	–	nC
Gate-to-Collector Charge	Q_{GC}		–	73.1	–	nC

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 20\text{ A}$ $R_G = 6\ \Omega$ $T_J = 25^\circ\text{C}$	–	53.5	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	311	–	
Rise Time	t_r		–	27.8	–	
Fall Time	t_f		–	189	–	
Turn-On Switching Loss	E_{on}	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 40\text{ A}$ $R_G = 6\ \Omega$ $T_J = 25^\circ\text{C}$	–	1.26	–	mJ
Turn-Off Switching Loss	E_{off}		–	1.36	–	
Total Switching Loss	E_{ts}		–	2.61	–	
Turn-On Delay Time	$t_{d(on)}$		–	58.2	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	258	–	
Rise Time	t_r		–	47.4	–	
Fall Time	t_f		–	122	–	
Turn-On Switching Loss	E_{on}		–	3.38	–	mJ
Turn-Off Switching Loss	E_{off}		–	1.7	–	
Total Switching Loss	E_{ts}		–	5.08	–	

AFGH4L40T120RWD

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 20\text{ A}$ $R_G = 6\ \Omega$ $T_J = 175^\circ\text{C}$	–	58.7	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	433	–	
Rise Time	t_r		–	39.4	–	
Fall Time	t_f		–	376	–	
Turn-On Switching Loss	E_{on}		–	2.01	–	mJ
Turn-Off Switching Loss	E_{off}		–	2.52	–	
Total Switching Loss	E_{ts}		–	4.53	–	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 40\text{ A}$ $R_G = 6\ \Omega$ $T_J = 175^\circ\text{C}$	–	65.7	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	343	–	
Rise Time	t_r		–	64.7	–	
Fall Time	t_f		–	233	–	
Turn-On Switching Loss	E_{on}		–	5.45	–	mJ
Turn-Off Switching Loss	E_{off}		–	3.04	–	
Total Switching Loss	E_{ts}		–	8.49	–	

DIODE CHARACTERISTICS

Diode Forward Voltage	V_F	$I_F = 40\text{ A}, T_J = 25^\circ\text{C}$	–	1.55	1.85	V
		$I_F = 40\text{ A}, T_J = 175^\circ\text{C}$	–	1.54	–	

DIODE SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 20\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	–	145	–	ns
Reverse Recovery Charge	Q_{rr}		–	2055	–	nC
Reverse Recovery Energy	E_{rec}		–	0.49	–	mJ
Peak Reverse Recovery Current	I_{RRM}		–	34	–	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 40\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	–	182	–	ns
Reverse Recovery Charge	Q_{rr}		–	3527	–	nC
Reverse Recovery Energy	E_{rec}		–	0.67	–	mJ
Peak Reverse Recovery Current	I_{RRM}		–	43.5	–	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 20\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}$ $T_J = 175^\circ\text{C}$	–	204	–	ns
Reverse Recovery Charge	Q_{rr}		–	3606	–	nC
Reverse Recovery Energy	E_{rec}		–	1.07	–	mJ
Peak Reverse Recovery Current	I_{RRM}		–	42.3	–	A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 40\text{ A},$ $di_F/dt = 500\text{ A}/\mu\text{s}$ $T_J = 175^\circ\text{C}$	–	253	–	ns
Reverse Recovery Charge	Q_{rr}		–	6542	–	nC
Reverse Recovery Energy	E_{rec}		–	1.52	–	mJ
Peak Reverse Recovery Current	I_{RRM}		–	57.6	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AFGH4L40T120RWD

TYPICAL CHARACTERISTICS

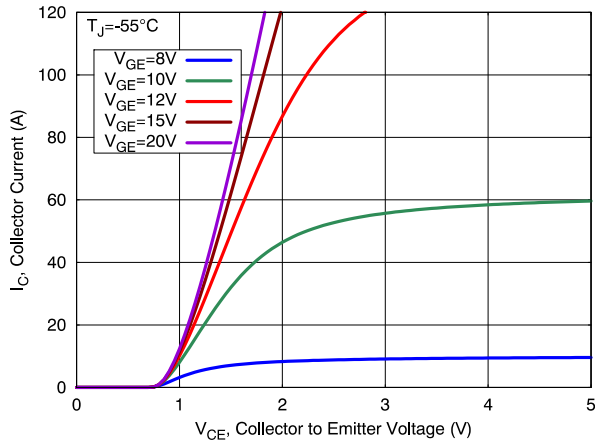


Figure 1. Output Characteristics

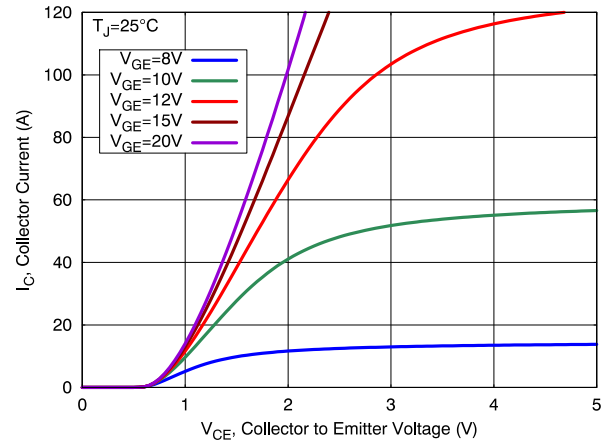


Figure 2. Output Characteristics

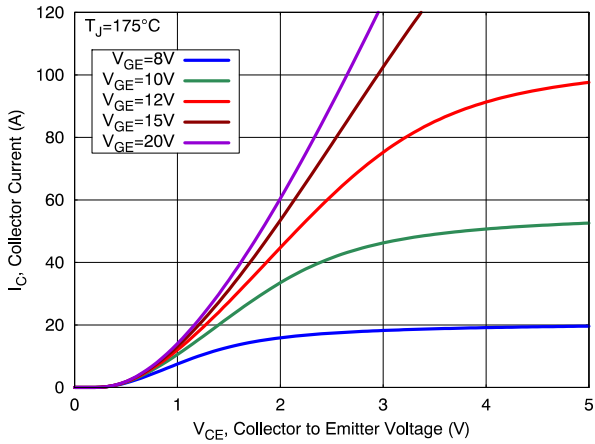


Figure 3. Output Characteristics

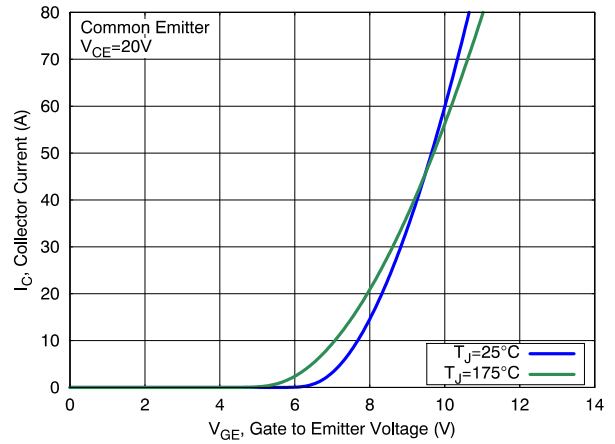


Figure 4. Transfer Characteristics

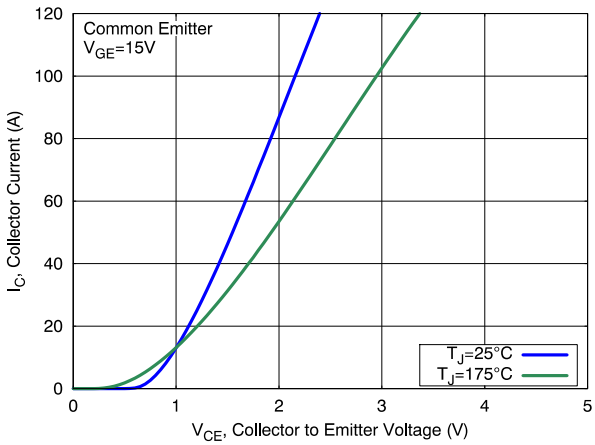


Figure 5. Saturation Characteristics

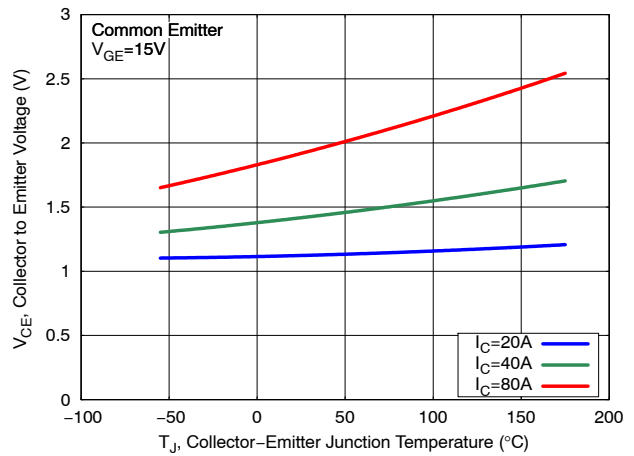


Figure 6. Saturation Voltage vs. Junction Temperature

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TYPICAL CHARACTERISTICS

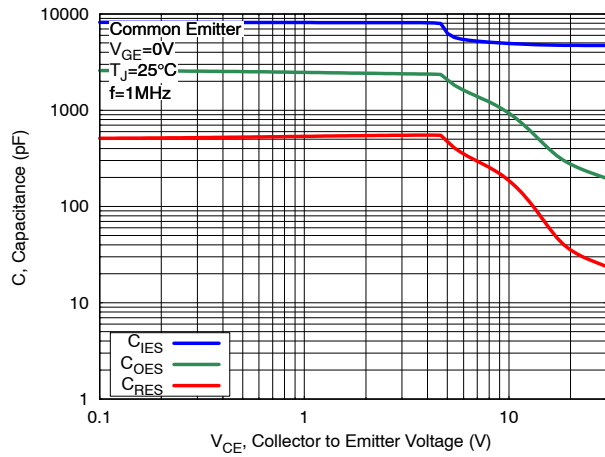


Figure 7. Capacitance Characteristics

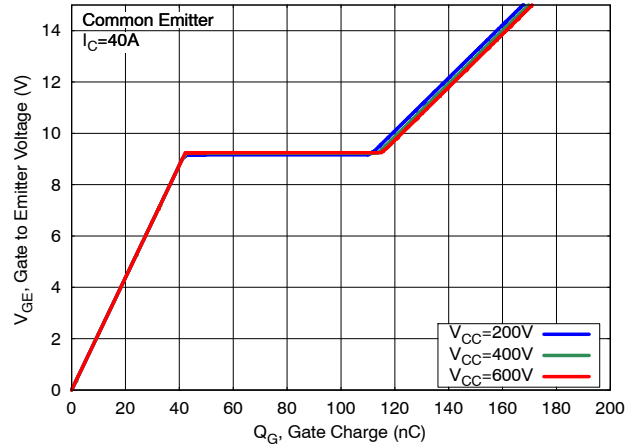


Figure 8. Gate Charge Characteristics

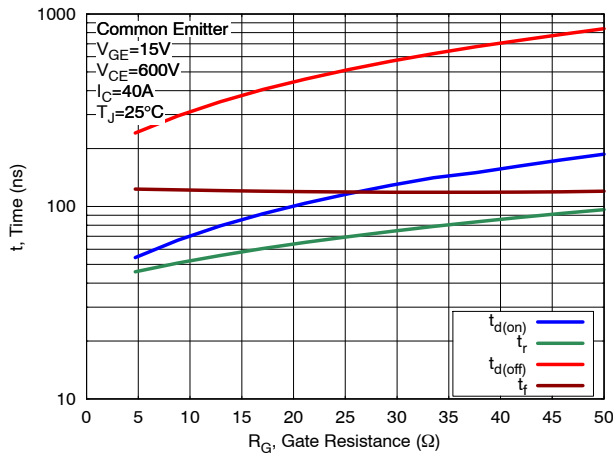


Figure 9. Switching Time vs Gate Resistance

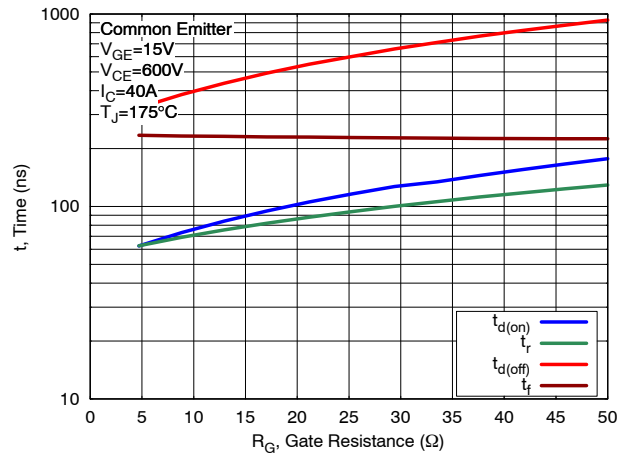


Figure 10. Switching Time vs Gate Resistance

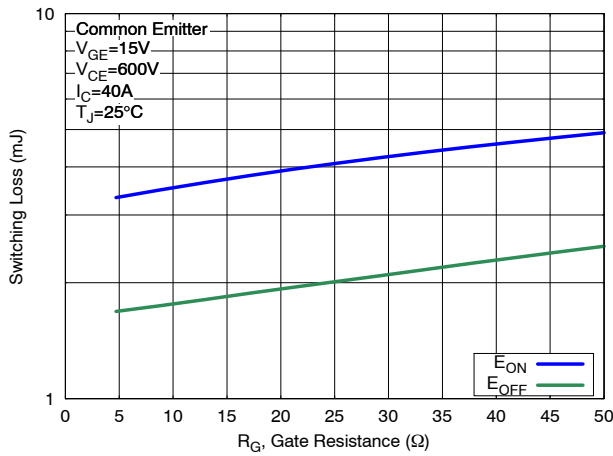


Figure 11. Switching Loss vs Gate Resistance

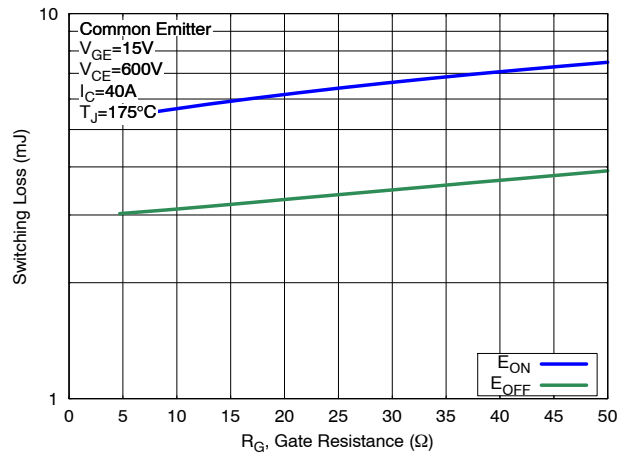


Figure 12. Switching Loss vs Gate Resistance

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TYPICAL CHARACTERISTICS

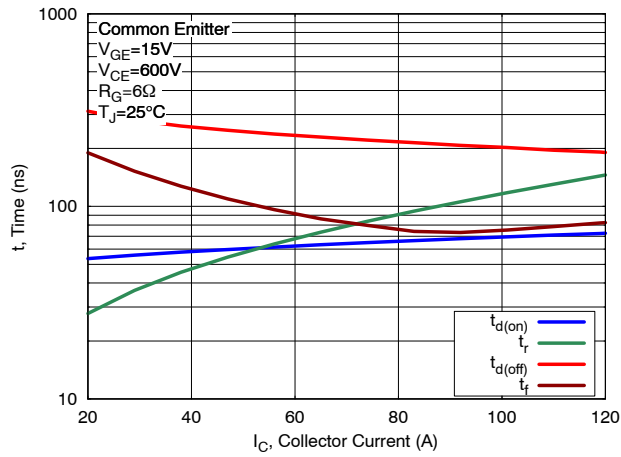


Figure 13. Switching Time vs Collector Current

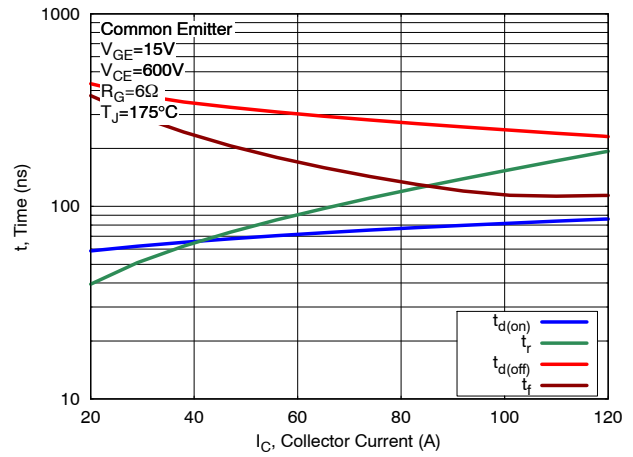


Figure 14. Switching Time vs Collector Current

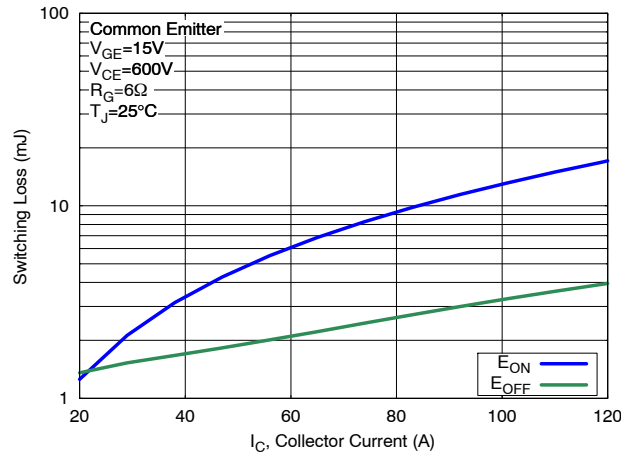


Figure 15. Switching Loss vs Collector Current

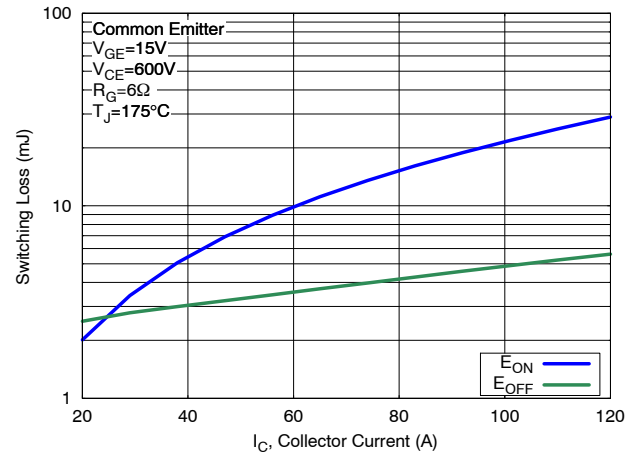


Figure 16. Switching Loss vs Collector Current

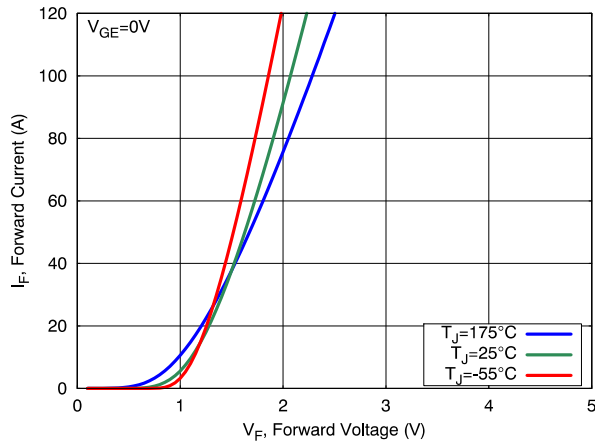


Figure 17. Diode Forward Characteristics

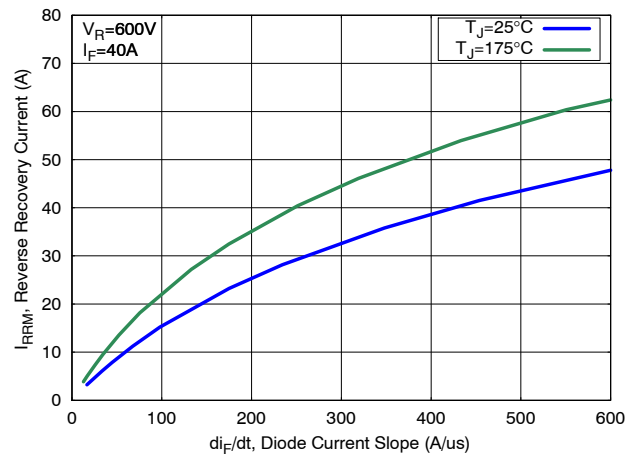


Figure 18. Diode Reverse Recovery Current

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TYPICAL CHARACTERISTICS

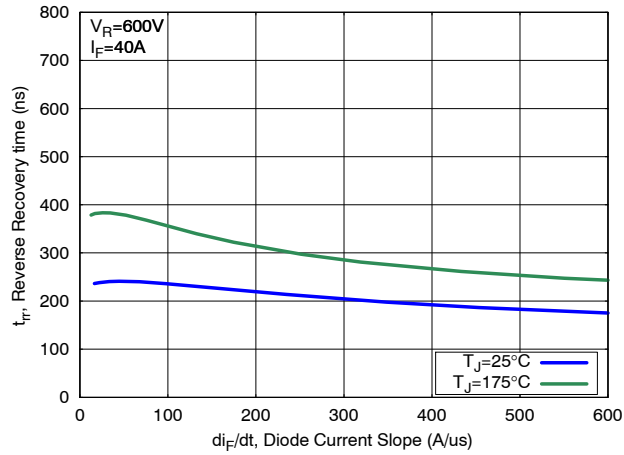


Figure 19. Diode Reverse Recovery Time

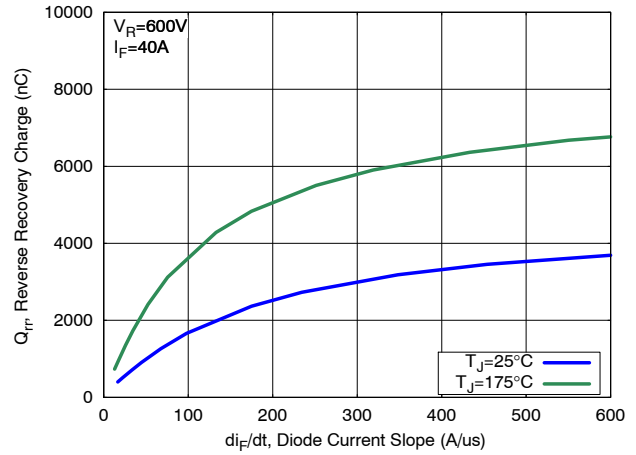


Figure 20. Diode Stored Charge Characteristics

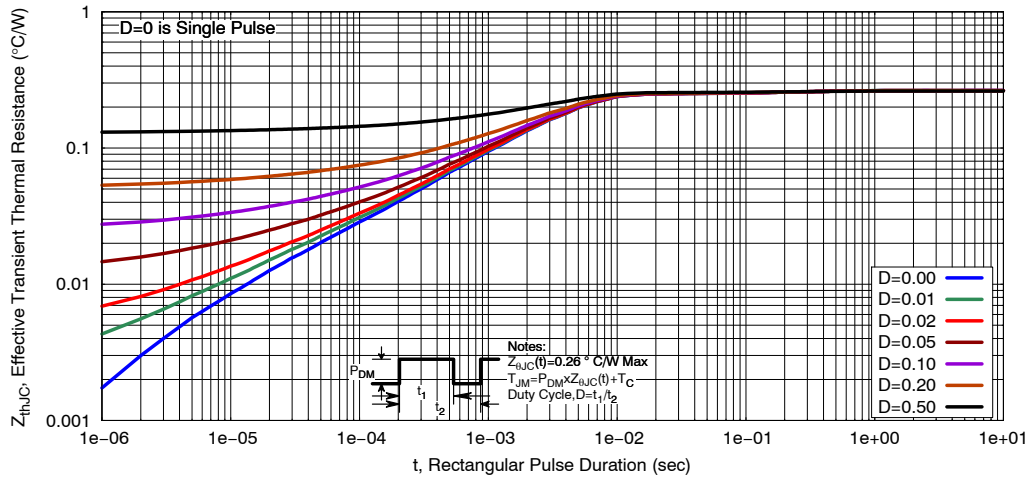


Figure 21. Transient Thermal Impedance of IGBT

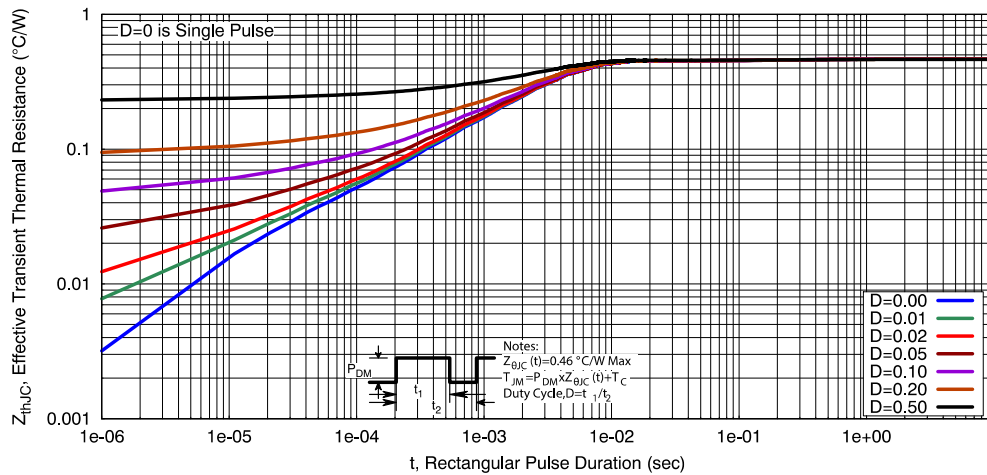


Figure 22. Transient Thermal Impedance of Diode

TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019


NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
 B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
 C. ALL DIMENSIONS ARE IN MILLIMETERS.
 D. DRAWING CONFORMS TO ASME Y14.5-2009.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

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